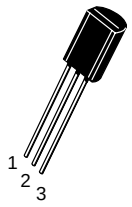
One Watt Darlington Transistors

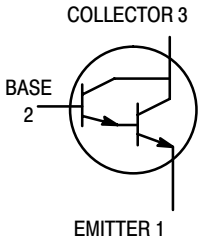
NPN Silicon

MPSW45
MPSW45A*

***ON Semiconductor Preferred Device**



CASE 29–10, STYLE 1
TO–92 (TO–226AE)



MAXIMUM RATINGS

Rating	Symbol	MPSW45	MPSW45A	Unit
Collector–Emitter Voltage	V_{CES}	40	50	Vdc
Collector–Base Voltage	V_{CBO}	50	60	Vdc
Emitter–Base Voltage	V_{EBO}	12	12	Vdc
Collector Current — Continuous	I_C	1.0	1.0	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 8.0		Watts mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)	 MPSW45 MPSW45A	$V_{(BR)CES}$	 40 50	 — —	Vdc
Collector–Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	 MPSW45 MPSW45A	$V_{(BR)CBO}$	 50 60	 — —	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	12	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 40 Vdc, I_E = 0)	 MPSW45 MPSW45A	I_{CBO}	 — —	 100 100	nAdc
Emitter Cutoff Current (V_{EB} = 10 Vdc, I_C = 0)		I_{EBO}	—	100	nAdc

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

March, 2001 – Rev. 1
Publication Order Number:
MPSW45/D

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS[1]				
DC Current Gain (I_C = 200 mAdc, V_{CE} = 5.0 Vdc) (I_C = 500 mAdc, V_{CE} = 5.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 5.0 Vdc)	h_{FE}	 25,000 15,000 4,000	 150,000 — —	—
Collector–Emitter Saturation Voltage (I_C = 1.0 Adc, I_B = 2.0 mAdc)	$V_{CE(sat)}$	—	1.5	Vdc
Base–Emitter Saturation Voltage (I_C = 1.0 Adc, I_B = 2.0 mAdc)	$V_{BE(sat)}$	—	2.0	Vdc
Base–Emitter On Voltage (I_C = 1.0 Adc, V_{CE} = 5.0 Vdc)	$V_{BE(on)}$	—	2.0	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product (I_C = 200 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	f_T	100	—	MHz
Collector–Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	6.0	pF

1. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

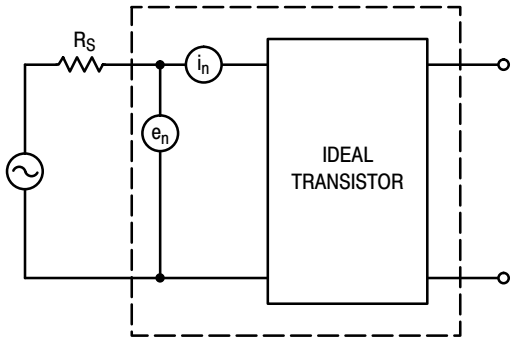


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

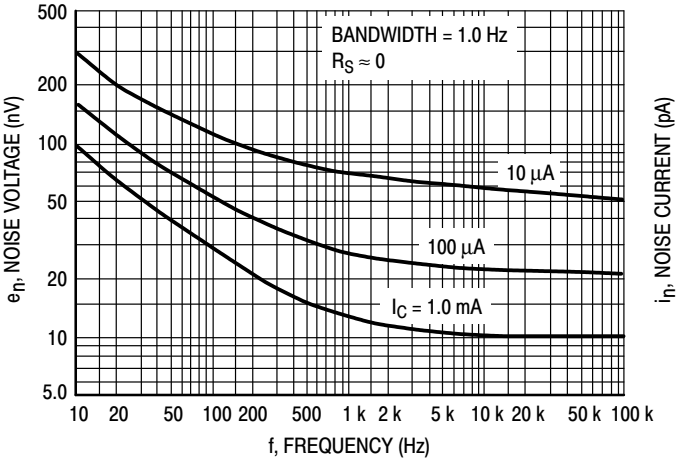


Figure 2. Noise Voltage

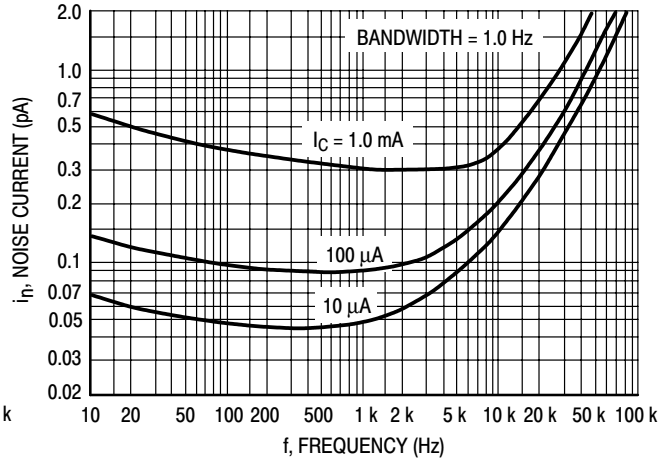


Figure 3. Noise Current

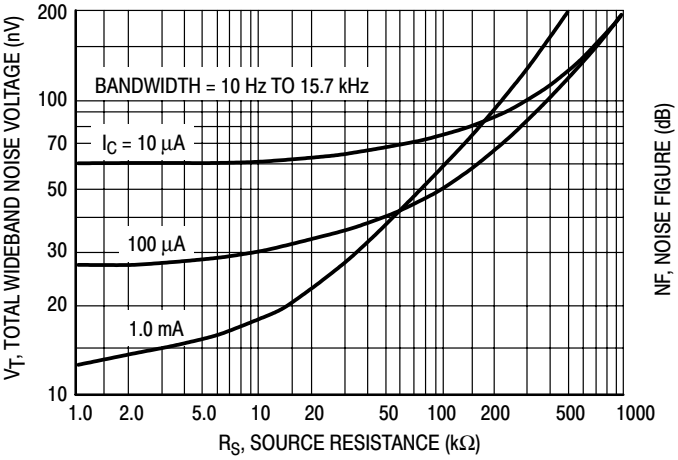


Figure 4. Total Wideband Noise Voltage

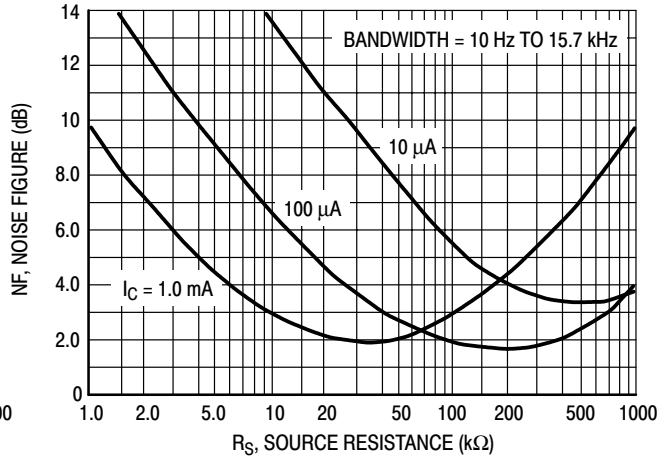


Figure 5. Wideband Noise Figure

SMALL−SIGNAL CHARACTERISTICS

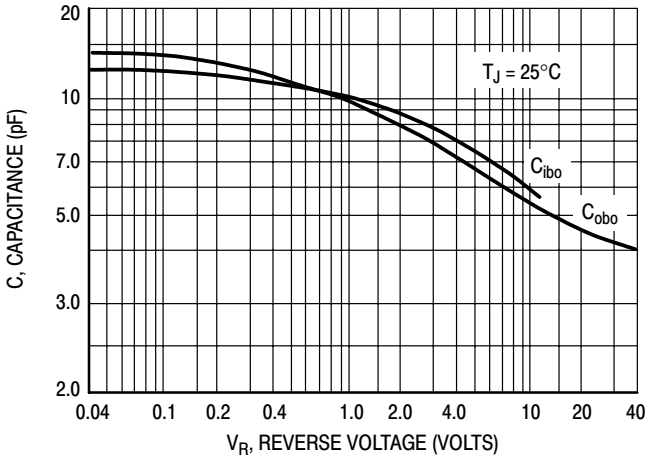


Figure 6. Capacitance

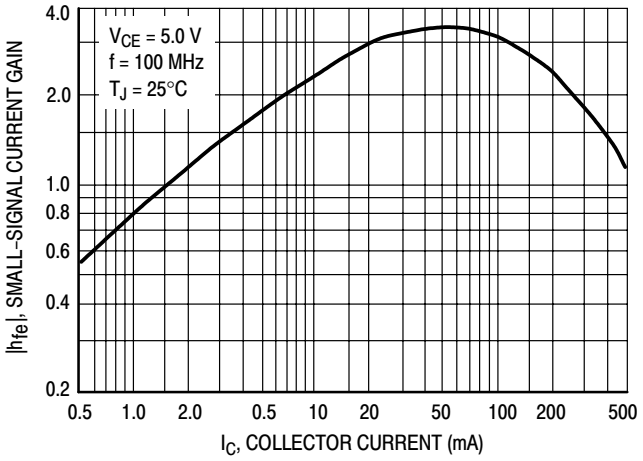


Figure 7. High Frequency Current Gain

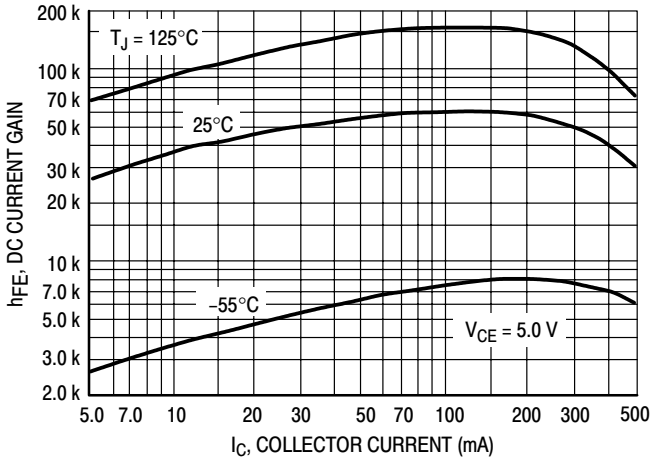


Figure 8. DC Current Gain

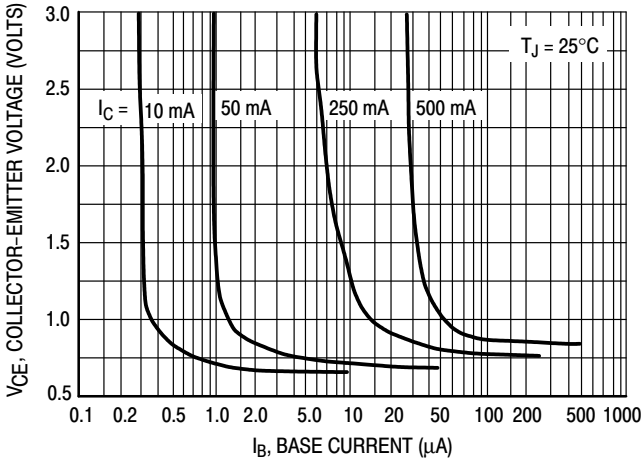


Figure 9. Collector Saturation Region

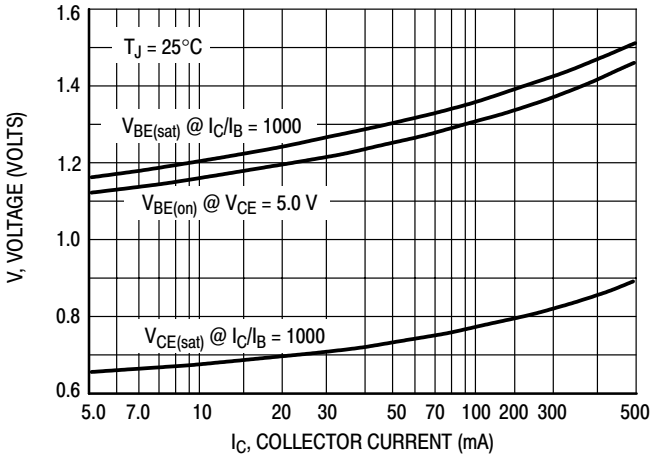


Figure 10. “On” Voltages

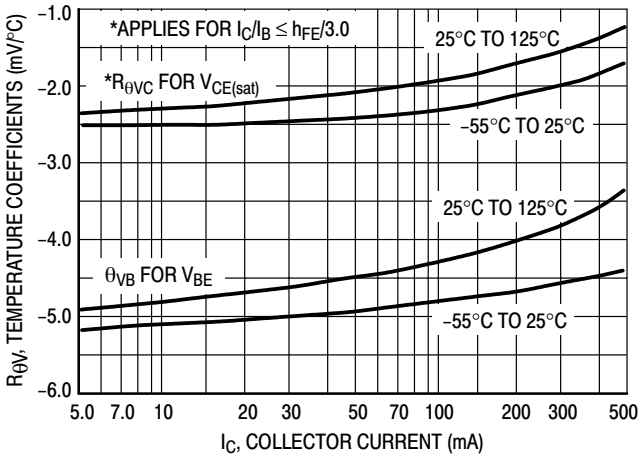


Figure 11. Temperature Coefficients

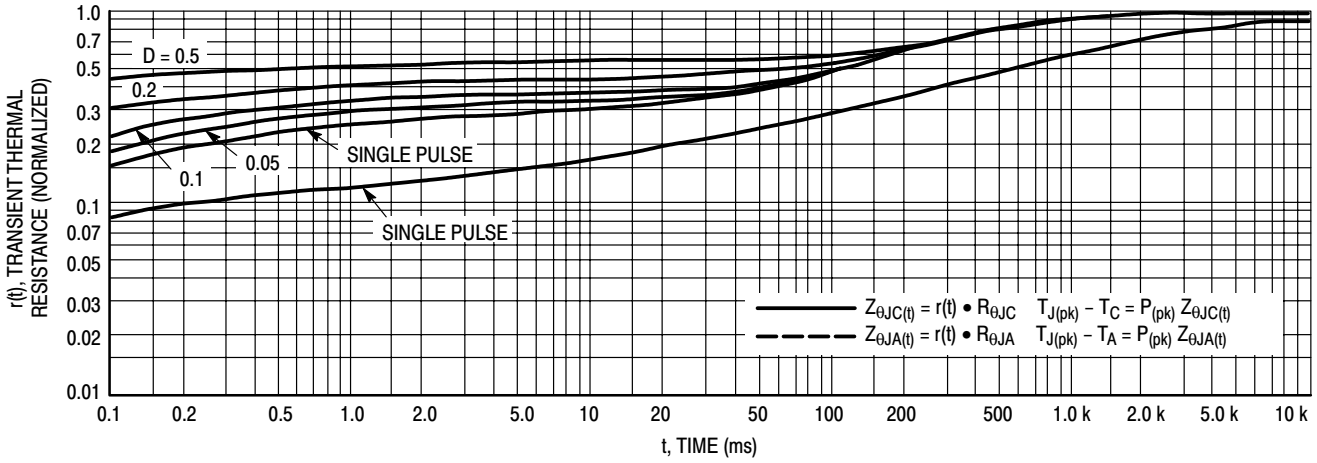
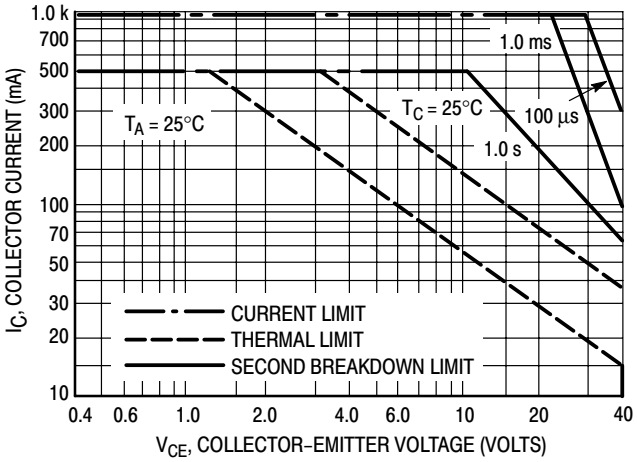


Figure 12. Thermal Response



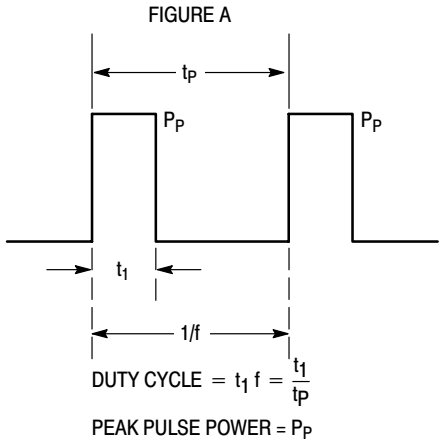


Figure 13. Active Region Safe Operating Area Design Note: Use of Transient Thermal Resistance Data